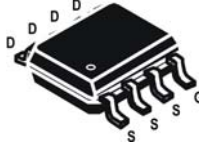
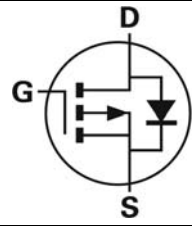


<b>V<sub>DSS</sub></b> , -30V <b>R<sub>DS(ON)</sub></b> , 60mΩ (max.) @ V <sub>GS</sub> =-10V <b>R<sub>DS(ON)</sub></b> , 108mΩ (max.) @ V <sub>GS</sub> =-4.5V <b>I<sub>D</sub></b> , -6.1A	<b>SOP-8</b> 	

Description	Features
<p>The SGP3036S is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent R<sub>DS(ON)</sub> and gate charge for most of the synchronous buck converter applications.</p> <p>The SGP3036S meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.</p>	<ul style="list-style-type: none"> <li>• Low On-Resistance</li> <li>• Low Input Capacitance</li> <li>• Low Miller Charge</li> <li>• Low Input / Output Leakage</li> <li>• Pb-free lead plating; RoHS compliant</li> </ul>
	Applications
	<ul style="list-style-type: none"> <li>• Motor / Body Load Control</li> <li>• Automotive Systems</li> <li>• Load Switch</li> <li>• DC-DC converters and Off-line UPS</li> </ul>

### Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGP3036S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

### Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	T <sub>C</sub> =25°C	-6.1
		T <sub>C</sub> =70°C	-4.9
Drain Current-Pulsed <sup>Note 1</sup>	I <sub>DM</sub>	-13	A
Drain Current-Continuous	I <sub>D</sub>	T <sub>A</sub> =25°C	-5.1
		T <sub>A</sub> =70°C	-4.1
Avalanche Current, L=0.1mH	I <sub>AS</sub>	20	A
Avalanche Energy, L=0.1mH <sup>Note 3</sup>	E <sub>AS</sub>	60	mJ
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> =25°C	2.1
		T <sub>C</sub> =70°C	1.3
		T <sub>A</sub> =25°C	1.5
		T <sub>A</sub> =70°C	0.9
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C
Operating Junction Temperature Range	T <sub>J</sub>	-55 to +150	°C

### Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>Note 1</sup>	R <sub>θJA</sub>	Steady State	-	-	85	°C/W
Maximum Junction-to-Case	R <sub>θJC</sub>	Steady State	-	-	60	°C/W

## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250μA	-1	-1.5	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>DS</sub> =-8A	-	-	60	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>DS</sub> =-4A	-	-	108	
Forward Transconductance <sup>Note 1</sup>	g <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-6A	-	5.8	-	S


DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1MHz	-	626	-	pF
Output Capacitance	C <sub>oss</sub>		-	264	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	101	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =-12V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-5A	-	8.8	-	ns
Rise Time	t <sub>r</sub>		-	16.2	-	
Turn-Off Delay Time	T <sub>d(off)</sub>		-	20.5	-	
Fall Time	t <sub>f</sub>		-	21.1	-	
Total Gate Charge at 10V	Q <sub>g</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6A	-	6.2	-	nC
Gate to Source Gate Charge	Q <sub>gs</sub>		-	2.6	-	
Gate to Drain "Miller" Charge	Q <sub>gd</sub>		-	3	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-6A	-	-	-1.2	V
Body Diode Reverse Recovery Time	t <sub>S</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	-	-	-6.1	A
Body Diode Reverse Recovery Charge	I <sub>SM</sub>		-	-	-13	A

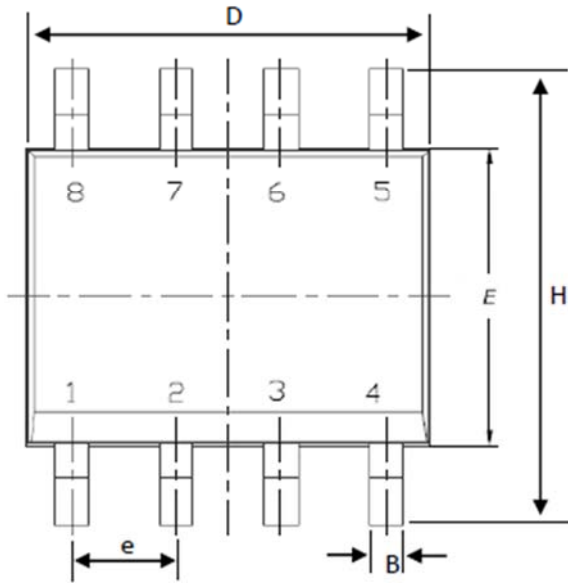
- Notes:**
- Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
  - R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design. R<sub>θJA</sub> shown below for single device operation on FR-4 in still air.
  - The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=-25V, V<sub>GS</sub>=-10V, L=0.1mH, I<sub>AS</sub>=-20A

**Marking Information**

SOP-8 (S)	Marking Rule
<p>Laser Marking</p>  <p>Diagram</p>	<p><u>Line 1</u> : Device Name SGP3036S</p> <p><u>Line 2</u> : Date Code YYMMXXX</p> <p>YY : Year Code MM : Month Code XXX : Serial Number</p>

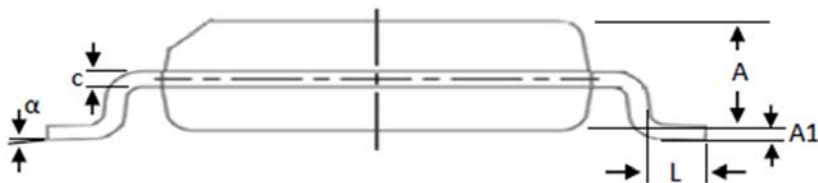
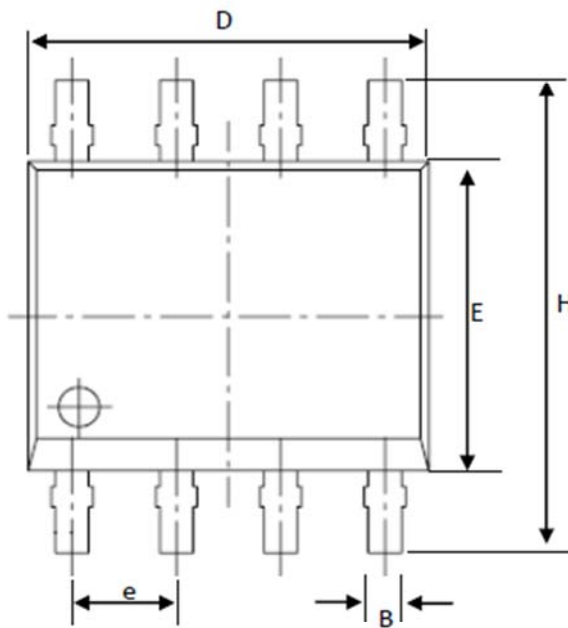
**Package of Dimension**

G-TYPE



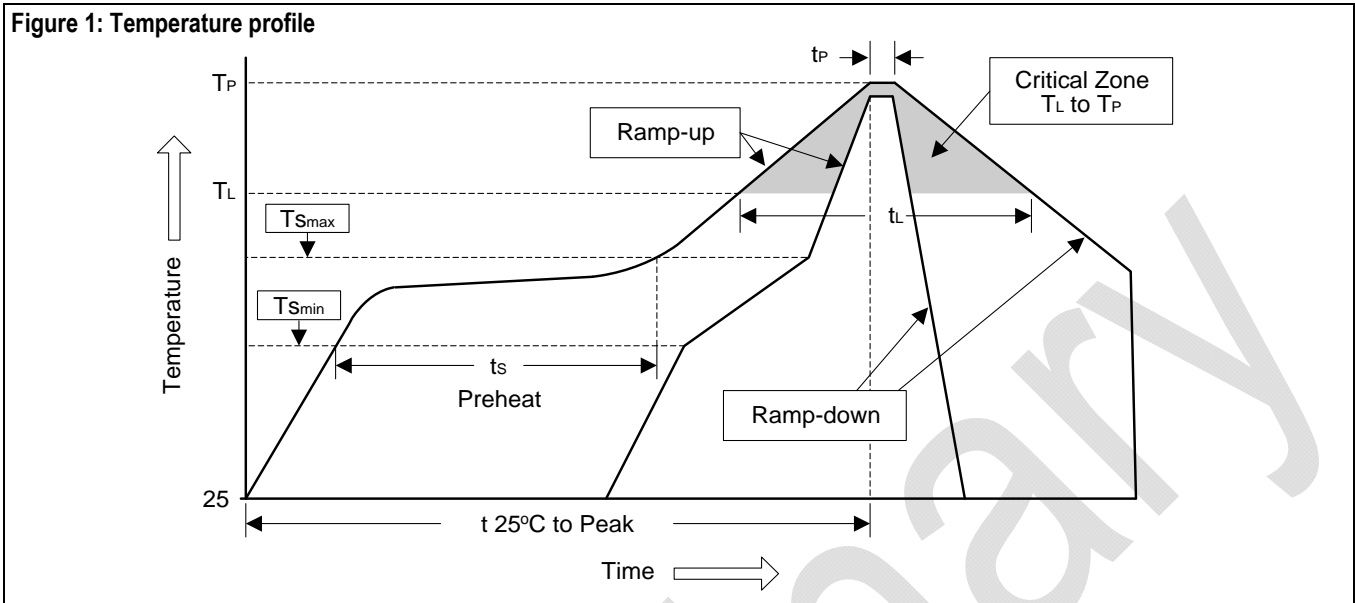
Symbol	Min	Nor	Max
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
B	0.31	0.41	0.51
c	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27	1.27	1.27
H	5.80	6.00	6.20
L	0.40	0.84	1.27
$\alpha$	0.00	4.00	8.00

B-TYPE



## Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (TL to TP)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T <sub>Smin</sub> )	100°C	150°C
- Temperature Max (T <sub>Smax</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
T <sub>Smax</sub> to TL		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (TL)	183°C	217°C
- Time (tL)	60 to 150 sec	60 to 150 sec
Peak Temperature (TP)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (tp)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

## Important Notice

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